

## ABSTRACT

[Abstract of the Disclosure]

5        Provided are a method for manufacturing a high k-dielectric oxide film, a  
capacitor having a dielectric film formed using the method, and a method for  
manufacturing the capacitor. A high k-dielectric oxide film is manufactured by (a)  
loading a semiconductor substrate in an ALD apparatus, (b) depositing a reaction  
material having a predetermined composition rate of a first element and a second  
10        element on the semiconductor substrate, and (c) forming a first high k-dielectric oxide  
film having the two elements on the semiconductor substrate by oxidizing the reaction  
material such that the first element and the second element are simultaneously oxidized.  
In this method, the size of an apparatus is reduced, productivity is enhanced, and  
manufacturing costs are lowered. Further, the high k-dielectric oxide film exhibits high  
dielectric constant and low leakage current and trap density. Thus, a capacitor  
15        including the high k-dielectric oxide film as a dielectric film also exhibits low leakage  
current and trap density.

[Representative Drawing]

FIG. 4